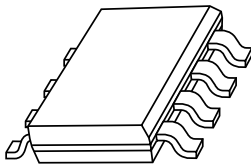


DATA SHEET



PHP222

Dual P-channel enhancement
mode MOS transistor

Preliminary specification
Supersedes data of 1998 Mar 24
File under Discrete Semiconductors, SC13

1998 Apr 01

Dual P-channel enhancement mode MOS transistor

PHP222

FEATURES

- Very low on-state resistance
- High-speed switching
- No secondary breakdown
- Low threshold.

APPLICATIONS

- Power management
- DC-DC converters
- General purpose switch.

DESCRIPTION

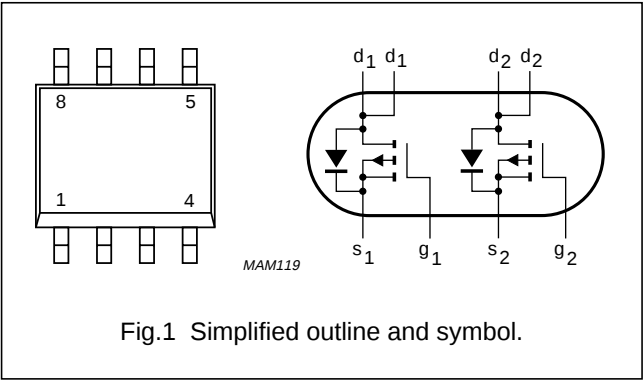
Two P-channel enhancement mode MOS transistors in an 8-pin SOT96-1 (SO8) SMD plastic package.

CAUTION

The device is supplied in an antistatic package.
The gate-source input must be protected against static discharge during transport or handling.

PINNING - SOT96-1 (SO8)

PIN	SYMBOL	DESCRIPTION
1	s ₁	source 1
2	g ₁	gate 1
3	s ₂	source 2
4	g ₂	gate 2
5	d ₂	drain 2
6	d ₂	drain 2
7	d ₁	drain 1
8	d ₁	drain 1



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DS}	drain-source voltage (DC)		–	–30	V
V _{SD}	source-drain diode forward voltage	I _S = –1.25 A; V _{GD} = 0	–	–1.3	V
V _{GSO}	gate-source voltage (DC)	open drain	–	±8	V
V _{GSt}	gate-source threshold voltage	I _D = –1 mA; V _{DS} = V _{GS}	–0.4	–	V
I _D	drain current (DC)	T _S = 80 °C	–	–3.2	A
R _{DSon}	drain-source on-state resistance	I _D = –1.6 A; V _{GS} = –2.5 V	–	220	mΩ
P _{tot}	total power dissipation	T _S = 80 °C	–	3.5	W

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per P-channel					
V_{DS}	drain-source voltage (DC)		–	–30	V
V_{GSO}	gate-source voltage (DC)	open drain	–	± 8	V
I_D	drain current (DC)	$T_s = 80\text{ }^{\circ}\text{C}$; note 1	–	–3.2	A
I_{DM}	peak drain current	note 2	–	–12.8	A
P_{tot}	total power dissipation	$T_s = 80\text{ }^{\circ}\text{C}$; note 3	–	3.5	W
		$T_{amb} = 25\text{ }^{\circ}\text{C}$; note 4	–	2.63	W
		$T_{amb} = 25\text{ }^{\circ}\text{C}$; note 5	–	1.14	W
		$T_{amb} = 25\text{ }^{\circ}\text{C}$; note 6	–	1.56	W
T_{stg}	storage temperature		–55	+150	$^{\circ}\text{C}$
T_j	operating junction temperature		–55	+150	$^{\circ}\text{C}$
Source-drain diode					
I_S	source current (DC)	$T_s = 80\text{ }^{\circ}\text{C}$	–	–2.7	A
I_{SM}	peak pulsed source current	note 2	–	–10.8	A

Notes

- T_s is the temperature at the soldering point of the drain lead.
- Pulse width and duty cycle limited by maximum junction temperature.
- Maximum permissible dissipation per MOS transistor. Both devices may be loaded up to 3.5 W at the same time.
- Maximum permissible dissipation per MOS transistor. Device mounted on a printed-circuit board with an $R_{th\ a-tp}$ (ambient to tie-point) of 27.5 K/W.
- Maximum permissible dissipation per MOS transistor. Device mounted on a printed-circuit board with an $R_{th\ a-tp}$ (ambient to tie-point) of 90 K/W.
- Maximum permissible dissipation if only one MOS transistor dissipates. Device mounted on a printed-circuit board with an $R_{th\ a-tp}$ (ambient to tie-point) of 90 K/W.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	20	K/W

Dual P-channel enhancement mode MOS transistor

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CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per P-channel						
V _{(BR)DSS}	drain-source breakdown voltage	V _{GS} = 0; I _D = −10 μA	−30	−	−	V
V _{GSth}	gate-source threshold voltage	V _{GS} = V _{DS} ; I _D = −1 mA	−0.4	−	−	V
I _{DSS}	drain-source leakage current	V _{GS} = 0; V _{DS} = −24 V	−	−	−100	nA
I _{GSS}	gate leakage current	V _{GS} = ±8 V; V _{DS} = 0	−	−	±100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = −4.5 V; I _D = −1.6 A	−	−	200	mΩ
		V _{GS} = −2.5 V; I _D = −1.6 A	−	−	220	mΩ
		V _{GS} = −1.8 V; I _D = −0.8 A	−	−	250	mΩ
C _{iss}	input capacitance	V _{GS} = 0; V _{DS} = −24 V; f = 1 MHz	−	696	−	pF
C _{oss}	output capacitance	V _{GS} = 0; V _{DS} = −24 V; f = 1 MHz	−	163	−	pF
C _{rss}	reverse transfer capacitance	V _{GS} = 0; V _{DS} = −24 V; f = 1 MHz	−	73	−	pF
Q _G	total gate charge	V _{GS} = −4.5 V; V _{DD} = −15 V; I _D = −1 A; T _{amb} = 25 °C	−	16	−	nC
Q _{GS}	gate-source charge	V _{DD} = −15 V; I _D = −1 A; T _{amb} = 25 °C	−	0.7	−	nC
Q _{GD}	gate-drain charge	V _{DD} = −15 V; I _D = −1 A; T _{amb} = 25 °C	−	4.1	−	nC
Switching times						
t _{d(on)}	turn-on delay time	V _{GS} = 0 to −8 V; V _{DD} = −20 V; I _D = −1 A; R _{gen} = 6 Ω	−	3.5	−	ns
t _r	rise time		−	4	−	ns
t _{on}	turn-on switching time		−	7.5	−	ns
t _{d(off)}	turn-off delay time	V _{GS} = −8 to 0 V; V _{DD} = −20 V; I _D = −1 A; R _{gen} = 6 Ω	−	90	−	ns
t _f	fall time		−	35	−	ns
t _{off}	turn-off switching time		−	125	−	ns
Source-drain diode						
V _{SD}	source-drain diode forward voltage	V _{GD} = 0; I _S = −1.25 A	−	−	−1.3	V
t _{rr}	reverse recovery time	I _S = −1.25 A; di/dt = 100 A/μs	−	65	−	ns

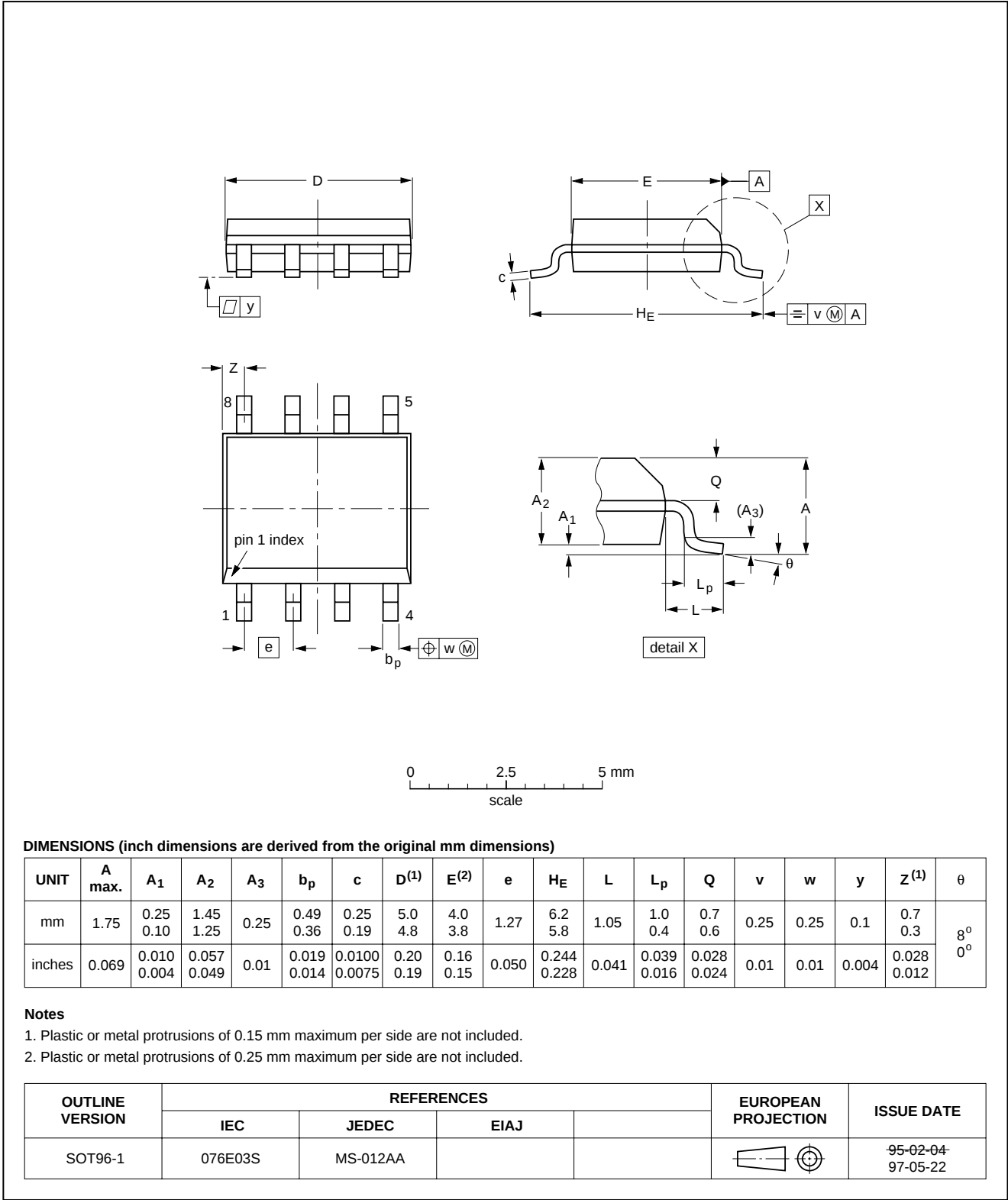
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PACKAGE OUTLINE

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



**Dual P-channel enhancement
mode MOS transistor**

PHP222**DEFINITIONS**

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

Dual P-channel enhancement
mode MOS transistor

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